

Description

The HXY60N02D uses advanced trench technology

to provide excellent RDS(ON), low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



TO252-2L

General Features

 $V_{DS} = 20V I_{D} = 60 A$

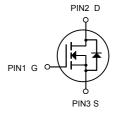
 $R_{DS(ON)}$ < 7.5m Ω @ V_{GS} =4.5V

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY60N02D	TO252-2L	60N02 XXX YYYY	2500

Absolute Maximum Ratings (T_c=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	20	V
Vgs	Gate-Source Voltage	±12	V
I _D	Drain Current-Continuous	60	А
I _D (100°C)	Drain Current-Continuous(Tc=100℃)	42	Α
Ідм	Pulsed Drain Current	210	А
P _D	Maximum Power Dissipation	60	W
	Derating factor	0.48	W/℃
Eas	Single pulse avalanche energy (Note 5)	200	mJ
T _J ,T _{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$
Rejc	Thermal Resistance,Junction-to-Case ^(Note 2)	2.1	°C/W



Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	age BV_{DSS} V_{GS} =0 V_{ID} =250 μ A		20	-	-	V
Zero Gate Voltage Drain Current	Ipss	V _{DS} =20V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	Igss	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _G S(th)	V _{DS} =V _{GS} ,I _D =250µA	0.5	0.75	1.0	V
	_	V _{GS} =4.5V, I _D =20 A	-	6	7.5	mΩ
Drain-Source On-State Resistance	RDS(ON)	V _{GS} =2.5V, I _D =15A		6.2	9	mΩ
Forward Transconductance	grs	V _{DS} =10V,I _D =20A	15	-	-	S
Input Capacitance	C _{lss}		-	2000	-	PF
Output Capacitance	Coss	V _{DS} =10V,V _{GS} =0V,	-	500	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	200	-	PF
Turn-on Delay Time	t _{d(on)}	V _{DD} =10V,I _D =2A,R _L =1Ω	-	6.4	-	nS
Turn-on Rise Time	t _r		-	17.2	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =4.5V, R_{G} =3 Ω	-	29.6	-	nS
Turn-Off Fall Time	t _f		-	16.8	-	nS
Total Gate Charge	Qg		-	27		nC
Gate-Source Charge	Qgs	V _{DS} =10V,I _D =20A,	-	6.5		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	6.4		nC
Diode Forward Voltage (Note 3)	Vsp	V _{GS} =0V,I _S =10A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	60	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 20A	-	25	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	24	-	nC
Forward Turn-On Time	ton	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** E_{AS} condition : Tj=25 $^{\circ}$ C,V_{DD}=10V,V_G=10V,L=0.5mH,Rg=25 Ω ,



Typical Electrical and Thermal Characteristics (Curves)

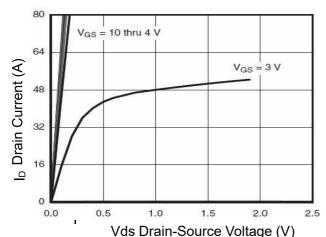
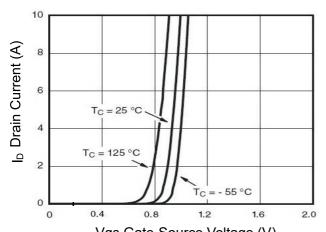


Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V) Figure 2 Transfer Characteristics

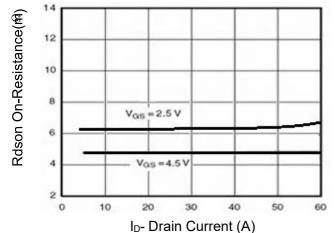


Figure 3 Rdson- Drain Current

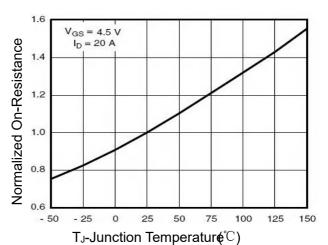
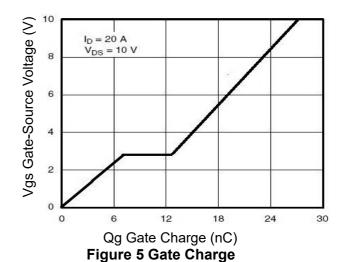


Figure 4 Rdson-JunctionTemperature



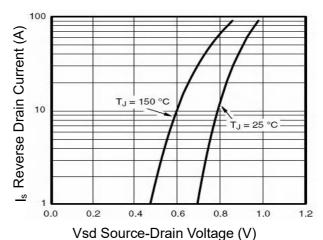


Figure 6 Source- Drain Diode Forward



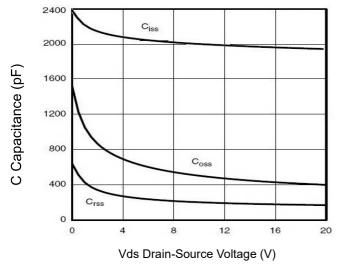
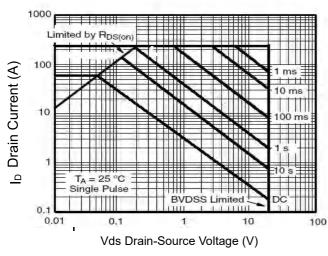


Figure 7 Capacitance vs Vds

Figure 9 Power De-rating



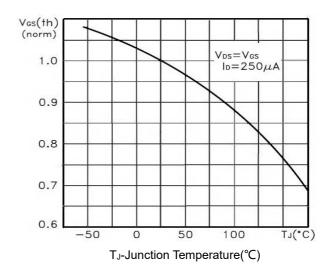
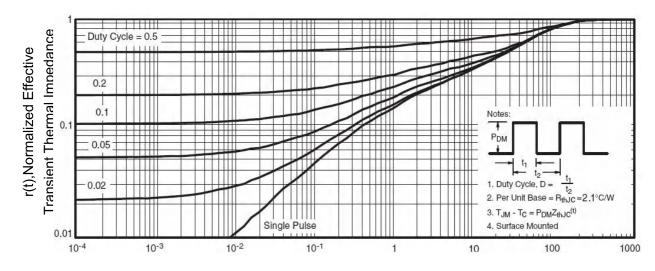


Figure 8 Safe Operation Area

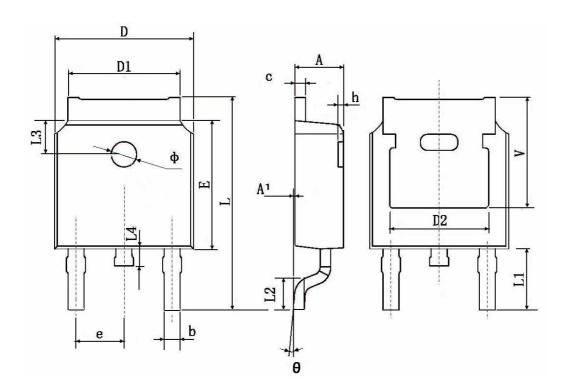
Figure 10 V_{GS(th)} vs Junction Temperature



Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance

TO252-2L Package Information



Councils of	Dimensions In Millimeters		Dimensions In Inches			
Symbol	Min.	Max.	Min.	Max.		
Α	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	0.483 TYP.		0.190 TYP.			
Е	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.900	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067		
L3	1.600	TYP.	0.063 TYP.			
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350 TYP. 0.21 ⁻¹		1 TYP.			

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